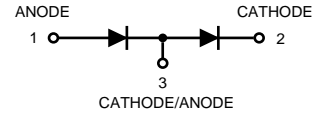
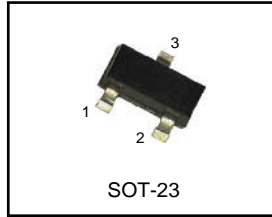


Dual Switching Diode

Lead free product

MMBD7000G



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	VR	100	Vdc
Peak Forward Current	IF	200	mAdc
Peak Forward Surge Current	IFM(surge)	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max.	Unit
Total Device Dissipation FR-5 Board ⁽¹⁾ TA=25°C Derate above 25°C	PD	225 1.8	mW mW / °C
Thermal Resistance, Junction to Ambient	R θ JA	556	°C / W
Total Device Dissipation Alumina Substrate, ⁽²⁾ TA=25°C Derate above 25°C	PD	300 2.4	mW mW / °C
Thermal Resistance, Junction to Ambient	R θ JA	417	°C / W
Junction and Storage Temperature	TJ,TSTG	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min.	Max.	Unit
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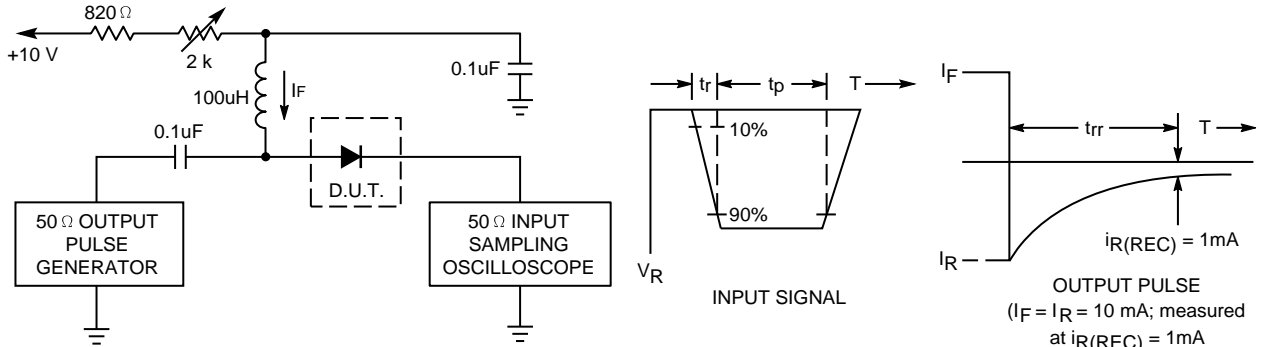
OFF CHARACTERISTICS

Reverse Breakdown Voltage (IBR=100uAdc)	V(BR)	100	-	Vdc
Forward Voltage (IF=1.0 mAdc) (IF=10 mAdc) (IF=100 mAdc)	VF	550 670 750	700 820 1100	mVdc
Reverse Voltage Leakage Current (VR=50 Vdc) (VR=100 Vdc,) (VR=50 Vdc, 125°C)	IR	- - -	1.0 3.0 100	uAdc
Diode Capacitance (VR=0, f=1.0MHZ)	CJ	-	1.5	pF
Reverse Recovery Time (IF=IR=10 mAdc, VR=5.0 Vdc, IR(REC)=1.0mAdc, RL=100Ω)	trr	-	4.0	nS

(1) FR-5=1.0 x 0.75 x 0.062in.

(2) Alumina=0.4 x 0.3 x 0.024in. 99.5% alumina.

FIGURE 1. RECOVERY TIME EQUIVALENT TEST CIRCUIT



- Notes: 1. A 2.0kΩ variable resistor adjusted for a Forward Current (I_F) of 10mA.
- 2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 10mA.
- 3. $t_p \gg t_{rr}$

FIGURE 2. FORWARD VOLTAGE

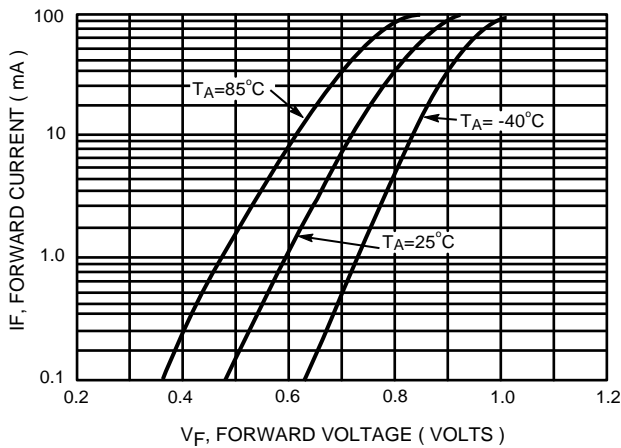


FIGURE 3. LEAKAGE CURRENT

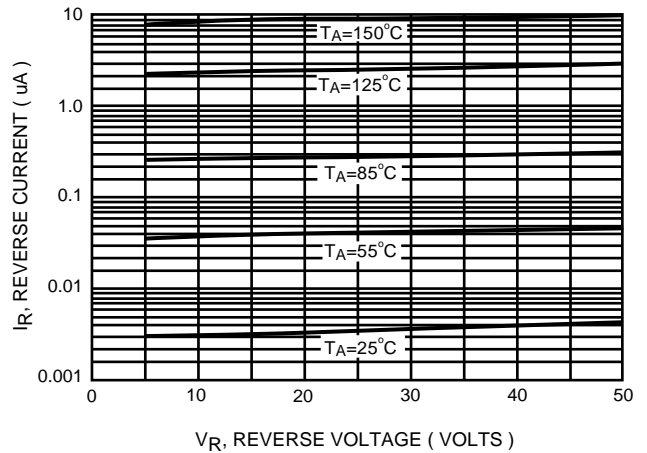


FIGURE 4. CAPACITANCE

